

Comment on “Density dependence of electron-spin polarization and relaxation in intrinsic GaAs at room temperature”

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(Dated: July 30, 2009)

We comment on the conclusion by Teng et al. [J. Phys. D: Appl. Phys. **42**, 135111 (2009)] that the Bir-Aronov-Pikus mechanism is more important than the D’yakonov-Perel’ mechanism at high carrier density in intrinsic bulk GaAs. We point out that the spin relaxation is solely from the D’yakonov-Perel’ mechanism.

Recently Teng et al. measured the density dependence of electron spin relaxation time in intrinsic bulk GaAs at room temperature.¹ They found that the electron spin relaxation time decreases with increasing carrier density in the carrier density regime $10^{17} < N_c < 2 \times 10^{18} \text{ cm}^{-3}$. Using the wrong formulae, they found that the D’yakonov-Perel’ (DP) spin relaxation time increases with increasing carrier density. As the Bir-Aronov-Pikus (BAP) spin relaxation time decreases with the carrier density, they concluded that the BAP mechanism is more important than the DP mechanism at high carrier density.

Their conclusion can not be correct. As shown in our recent paper² that the BAP mechanism is less important than the DP mechanism in almost all the intrinsic bulk III-V semiconductors. In fact, Teng et al. obtained such incorrect conclusion because they used wrong statistics: they applied the Boltzmann statistics to a high carrier density regime where E_F is comparable with or larger than $k_B T$. Then they obtained the increase of the DP spin relaxation time with elevating carrier density as using the Boltzmann statistics, the inhomogeneous broadening of the spin-orbit field $\langle \Omega_{\mathbf{k}}^2 \rangle$ does not change with carrier density. Furthermore, they used an incorrect formula that the electron-electron Coulomb scattering rate increases with carrier density as $1/\tau_p^{ee} \sim N_c^{0.3}$ for such high density in the experiment (The correct one can be found in Ref. 2). Therefore, they obtained that the DP spin relaxation time $\tau_{DP} \sim 1/(\langle \Omega_{\mathbf{k}}^2 \rangle \tau_p) \sim N_c^{0.3}$, which increases with increasing carrier density.

In fact in the *non-degenerate* (low carrier density) regime the DP spin relaxation time does increase with carrier density.² However, for the high carrier density in the experiment, the electron system is actually in *degenerate* regime (e.g., at $N_c = 10^{18} \text{ cm}^{-3}$, $E_F \simeq 2k_B T$). In degenerate regime, the electron-electron and electron-hole scatterings *decrease* with increasing carrier density.² Furthermore, the inhomogeneous broadening $\langle \Omega_{\mathbf{k}}^2 \rangle$ *increases* with carrier density, $\langle \Omega_{\mathbf{k}}^2 \rangle \sim k_F^6 \sim N_c^2$. Therefore the DP spin relaxation time $\tau_{DP} \sim 1/(\langle \Omega_{\mathbf{k}}^2 \rangle \tau_p)$ decreases rapidly with increasing carrier density in degenerate regime. There is *no way* that the DP spin relaxation time can increase with carrier density at such high carrier density in the experiment of Teng et al.¹

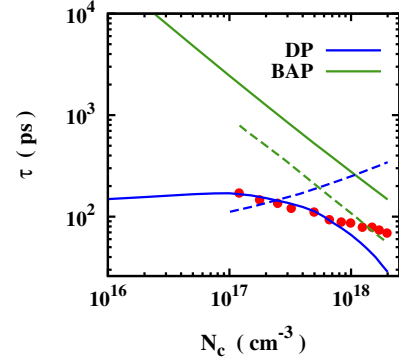


FIG. 1: (Color online) Carrier density N_c dependence of spin relaxation time in intrinsic bulk GaAs at room temperature. The red dots represent the experimental results by Teng et al.,¹ the blue (green) curves are the spin relaxation time limited by the DP (BAP) mechanism. The solid curves are calculated via the fully microscopic kinetic spin Bloch equation approach, whereas the dashed ones are from the calculation in the paper of Teng et al.¹

To check their results, we further calculate the spin relaxation time via the fully microscopic kinetic spin Bloch equation approach^{2,3} which has been applied to many situations with good agreement with experiments.⁴ This many-body approach includes all the relevant scatterings such as the electron-impurity, electron-phonon, electron-electron Coulomb, electron-hole Coulomb and electron-hole exchange scatterings explicitly.^{2,3} Our results are plotted in Fig. 1 as solid curves. For comparison the results of Teng et al. are plotted as dashed curves. It is noted that the DP spin relaxation time from the fully microscopic approach decreases with carrier density for $N_c > 10^{17} \text{ cm}^{-3}$, whereas it increases with increasing carrier density at lower densities. This further confirms the above conclusion that the DP spin relaxation time can only *decrease* with carrier density in the experiment of Teng et al.

To further check the BAP spin relaxation time in the paper of Teng et al.,¹ we calculate the same quantity via the fully microscopic kinetic spin Bloch equation approach.² We find that Teng et al. also overestimated the BAP mechanism (see Fig. 1). The possible reason is

that Teng et al. used larger electron-hole exchange interaction constants to fit their experimental results. However, these constants have been measured accurately and can be found in standard handbooks such as *Landolt-Börnstein*.⁵ In our fully microscopic calculation, all the material parameters are taken from *Landolt-Börnstein*.⁵

From the results in Fig. 1, one can conclude that the experimental results can not be explained via the BAP mechanism, as the BAP spin relaxation time is much larger than the measured one. We then fit the experimental results via the DP mechanism. For the DP spin relaxation, there is only one free parameter, i.e., the Dresselhaus spin-orbit coupling constant γ_D which has not been unambiguously determined by experiment or theory. With this parameter (which actually scales the DP

spin relaxation time as $\tau_{DP} \propto \gamma_D^{-2}$), we fitted the experimental results. A best fitting at low carrier density gives $\gamma_D = 7.6 \text{ eV}\cdot\text{\AA}^3$. This value is close to the value fitted from other experiment ($\gamma_D = 8.2 \text{ eV}\cdot\text{\AA}^3$)² and that from recent *ab initio* calculation with GW approximation ($\gamma_D = 8.5 \text{ eV}\cdot\text{\AA}^3$).⁶ The calculation agrees well with the experimental results for carrier densities up to 10^{18} cm^{-3} . The discrepancy at high carrier density may come from overestimation of the carrier density in the experiment and/or the hot-electron effect due to optical excitation with excess carrier energy.

This work was supported by the Natural Science Foundation of China under Grant No. 10725417. We thank T. S. Lai for helpful discussions.

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